

#### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

| BV <sub>DSS</sub> | Rds(ON) Max                 | I <sub>D</sub> Max<br>T <sub>A</sub> = +25°C |
|-------------------|-----------------------------|--|
| 60V               | 7.5Ω @ V <sub>GS</sub> = 5V | 0.23A  |

### **Features and Benefits**

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
  - https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (2N7002DWQ)

### **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance  $(R_{\text{DS(ON)}})$  yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Motor Control
- Power Management Functions

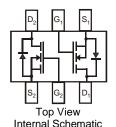
#### **Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Lead-Frame (Lead Free Plating). Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)

SOT363 (Standard)



Top View



#### **Ordering Information** (Note 4)

| Part Number   | Case              | Packaging          |
|---------------|-------------------|--------------------|
| 2N7002DW-7-F  | SOT363 (Standard) | 3,000/Tape & Reel  |
| 2N7002DW-13-F | SOT363 (Standard) | 10,000/Tape & Reel |

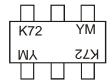
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

June 2021



### **Marking Information**



K72 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: I = 2021) M or  $\overline{M}$ = Month (ex: 9 = September)

#### Date Code Key

| Year  | 2004 |     | 2021  | 2022 | 2023  | 2024 | 2025 | 2026 | 2027 | 2028 | 2029 | 2030 |
|-------|------|-----|-------|------|-------|------|------|------|------|------|------|------|
| Code  | R    |     | ı     | J    | K     | L    | M    | N    | 0    | Р    | R    | S    |
| Month | lon  | Feb | Mar   | Anr  | May   | lun  | Jul  | Aug  | Sep  | Oct  | Nov  | Dec  |
| WOTH  | Jan  | reb | IVIAI | Apr  | iviay | Jun  | Jui  | Aug  | Sep  | OCI  | NOV  | Dec  |

# **Maximum Ratings** (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic   | Symbol           | Value   | Unit |                      |   |
|--|------------------|---|------|----------------------|---|
| Drain-Source Voltage                                   | V <sub>DSS</sub> | 60  | V    |                      |   |
| Drain-Gate Voltage R <sub>G</sub> s ≤ 1.0MΩ            |                  |   | Vdgr | 60                   | V |
| Gate-Source Voltage                                    |                  | Continuous  | Vgss | ±20                  | V |
| Gale-Source Vollage                                    | F                | Pulsed (Note 8)   | Vgss | ±40                  | V |
| Continuous Drain Current (Note 6) V <sub>GS</sub> = 5V | Steady<br>State  | $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$ $T_A = +100^{\circ}C$ |      | 0.23<br>0.18<br>0.14 | А |
| Maximum Continuous Body Diode Forward Curre            |                  | ls  | 0.23 | Α                    |   |
| Pulsed Drain Current (10µs Pulse, Duty Cycle =         | I <sub>DM</sub>  | 0.8   | Α    |                      |   |

### Thermal Characteristics (@ TA = +25°C, unless otherwise specified.)

| Characteristic                                   |                         | Symbol   | Value       | Unit |
|--|-------------------------|----------|-------------|------|
|  | T <sub>A</sub> = +25°C  |          | 0.31        |      |
| Total Power Dissipation (Note 5)                 | T <sub>A</sub> = +70°C  | $P_D$    | 0.2         | W    |
|  | T <sub>A</sub> = +100°C |          | 0.12        |      |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State            | RθJA     | 410         | °C/W |
|  | T <sub>A</sub> = +25°C  |          | 0.4         |      |
| Total Power Dissipation (Note 6)                 | T <sub>A</sub> = +70°C  | PD       | 0.25        | W    |
|  | T <sub>A</sub> = +100°C |          | 0.15        |      |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State            | RθJA     | 318         | °C/W |
| Thermal Resistance, Junction to Case (Note 6)    | Steady State            | Rejc     | 135         | °C/W |
| Operating and Storage Temperature Range          |                         | TJ, TSTG | -55 to +150 | °C   |

Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
   Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
   Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.



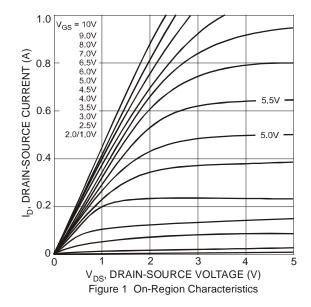
# Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

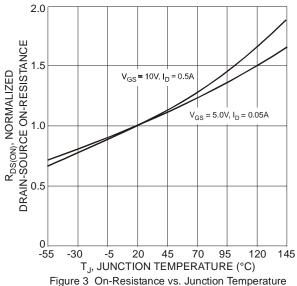
| Characteristic                    |   | Symbol              | Min | Тур        | Max         | Unit | Test Condition  |
|-----------------------------------|---|---------------------|-----|------------|-------------|------|---|
| OFF CHARACTERISTICS (Note 7)      |   |                     |     |            |             |      |   |
| Drain-Source Breakdown Voltage    |   | BVDSS               | 60  | 70         |             | ٧    | $V_{GS} = 0V, I_{D} = 10\mu A$  |
| Zero Gate Voltage Drain Current   | @ T <sub>C</sub> = +25°C<br>@ T <sub>C</sub> = +125°C | IDSS                | _   | _          | 1.0<br>500  | μΑ   | V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V   |
| Gate-Body Leakage                 |   | Igss                | _   | _          | ±10         | nA   | $V_{GS} = \pm 20V$ , $V_{DS} = 0V$  |
| ON CHARACTERISTICS (Note 7)       |   |                     |     |            |             |      |   |
| Gate Threshold Voltage            |   | V <sub>GS(TH)</sub> | 1.0 | _          | 2.0         | ٧    | $V_{DS} = V_{GS}$ , $I_D = 250\mu A$  |
| Static Drain-Source On-Resistance | @ T <sub>J</sub> = +25°C                              | RDS(ON)             | _   | 3.2<br>4.4 | 7.5<br>13.5 | Ω    | $V_{GS} = 5.0V, I_{D} = 0.05A$  |
|                                   | @ $T_J = +125$ °C                                     |                     |     |            |             |      | $V_{GS} = 10V, I_{D} = 0.5A$  |
| On-State Drain Current            |   | I <sub>D(ON)</sub>  | 0.5 | 1.0        | _           | Α    | $V_{GS} = 10V, V_{DS} = 7.5V$   |
| Forward Transconductance          |   | <b>g</b> FS         | 80  | _          | _           | mS   | $V_{DS} = 10V, I_D = 0.2A$  |
| Diode Forward Voltage             |   | VsD                 | _   | 0.78       | 1.5         | V    | V <sub>G</sub> S = 0V, I <sub>S</sub> = 115mA   |
| DYNAMIC CHARACTERISTICS (Note 8)  |   |                     |     |            |             |      |   |
| Input Capacitance                 |   | Ciss                | _   | 22         | 50          | pF   |   |
| Output Capacitance                |   | Coss                | _   | 11         | 25          | pF   | V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V<br>f = 1.0MHz                                 |
| Reverse Transfer Capacitance      |   | Crss                | _   | 2.0        | 5.0         | pF   | 1 = 1.0WH12   |
| Turn-On Delay Time                |   | tD(ON)              | _   | 7.0        | 20          |      | $V_{DD} = 30V, I_D = 0.2A,$   |
| Turn-Off Delay Time               |   | t <sub>D(OFF)</sub> | _   | 11.0       | 20          | ns   | $\begin{aligned} R_L &= 150\Omega, \ V_{GEN} = 10V, \\ R_{GEN} &= 25\Omega \end{aligned}$ |

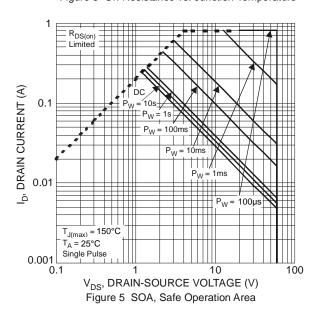
Notes:

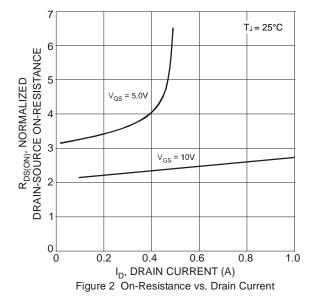
<sup>7.</sup> Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.

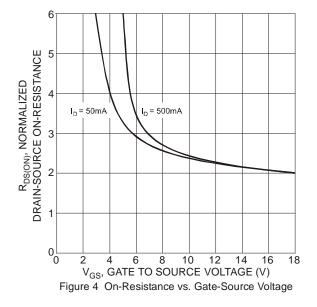








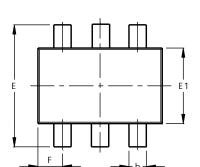


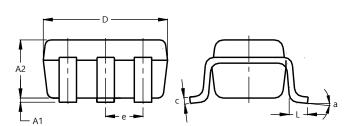




### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.





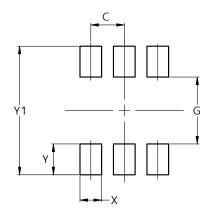
| SC    | SOT363 (Standard)    |      |       |  |  |  |  |  |
|-------|----------------------|------|-------|--|--|--|--|--|
| Dim   | Min                  | Max  | Тур   |  |  |  |  |  |
| A1    | 0.00                 | 0.10 | 0.05  |  |  |  |  |  |
| A2    | 0.80                 | 1.00 | 0.90  |  |  |  |  |  |
| b     | 0.10                 | 0.35 | 0.225 |  |  |  |  |  |
| С     | 0.08                 | 0.22 | 0.15  |  |  |  |  |  |
| D     | 1.80                 | 2.20 | 2.00  |  |  |  |  |  |
| Е     | 2.00                 | 2.45 | 2.225 |  |  |  |  |  |
| E1    | 1.15                 | 1.35 | 1.25  |  |  |  |  |  |
| е     | -                    | 1    | 0.65  |  |  |  |  |  |
| F     | 0.25                 | 0.45 | 0.35  |  |  |  |  |  |
| L     | 0.25                 | 0.46 | 0.355 |  |  |  |  |  |
| а     | 0°                   | 8°   |       |  |  |  |  |  |
| All I | All Dimensions in mm |      |       |  |  |  |  |  |

# **Suggested Pad Layout**

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$ 

#### SOT363 (Standard)

SOT363 (Standard)



| Dimensions    | Value   |  |  |
|---------------|---------|--|--|
| Dillielisions | (in mm) |  |  |
| С             | 0.650   |  |  |
| G             | 1.300   |  |  |
| Х             | 0.420   |  |  |
| Y             | 0.600   |  |  |
| Y1            | 2.500   |  |  |



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